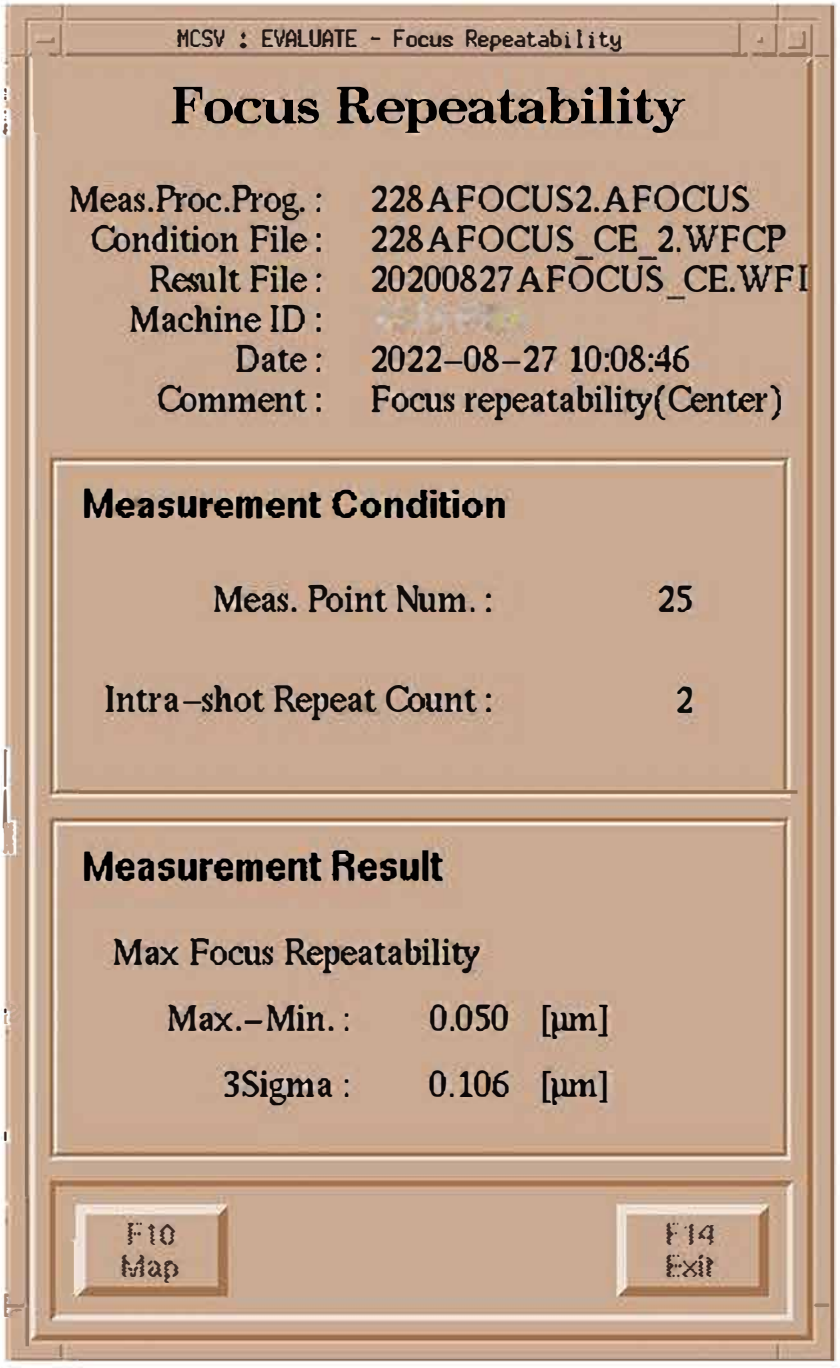
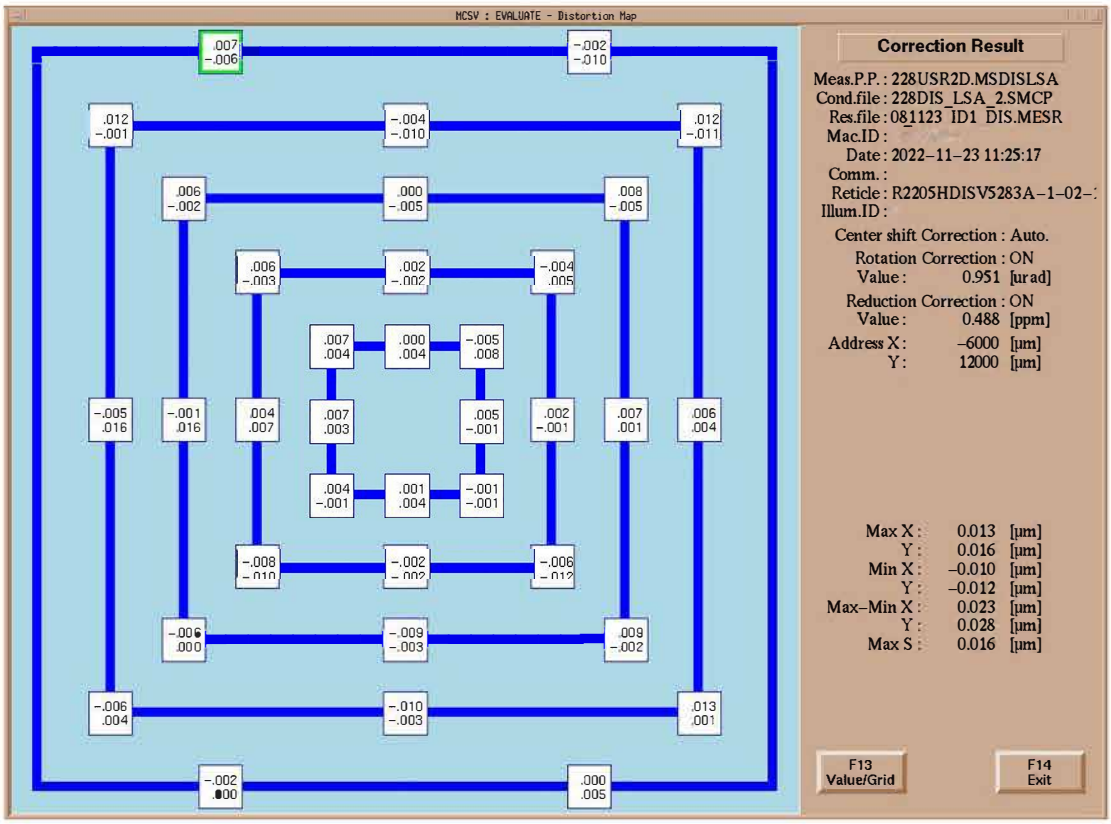
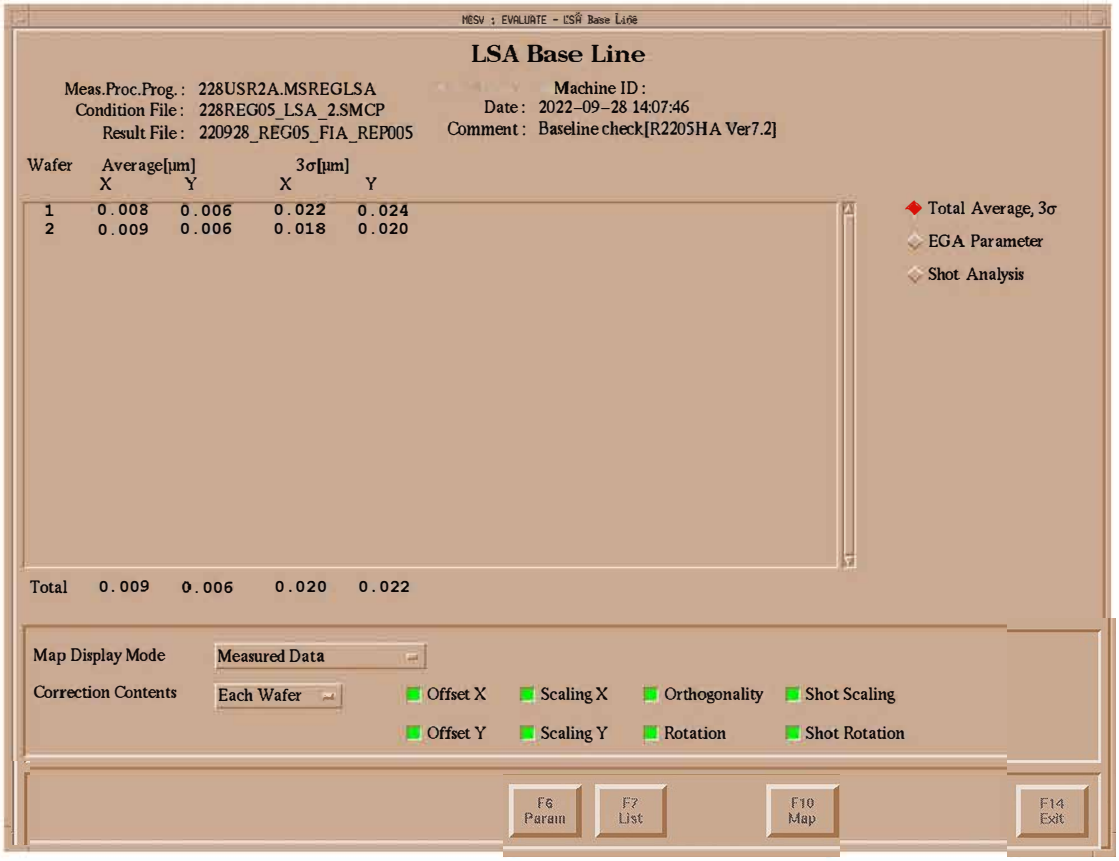
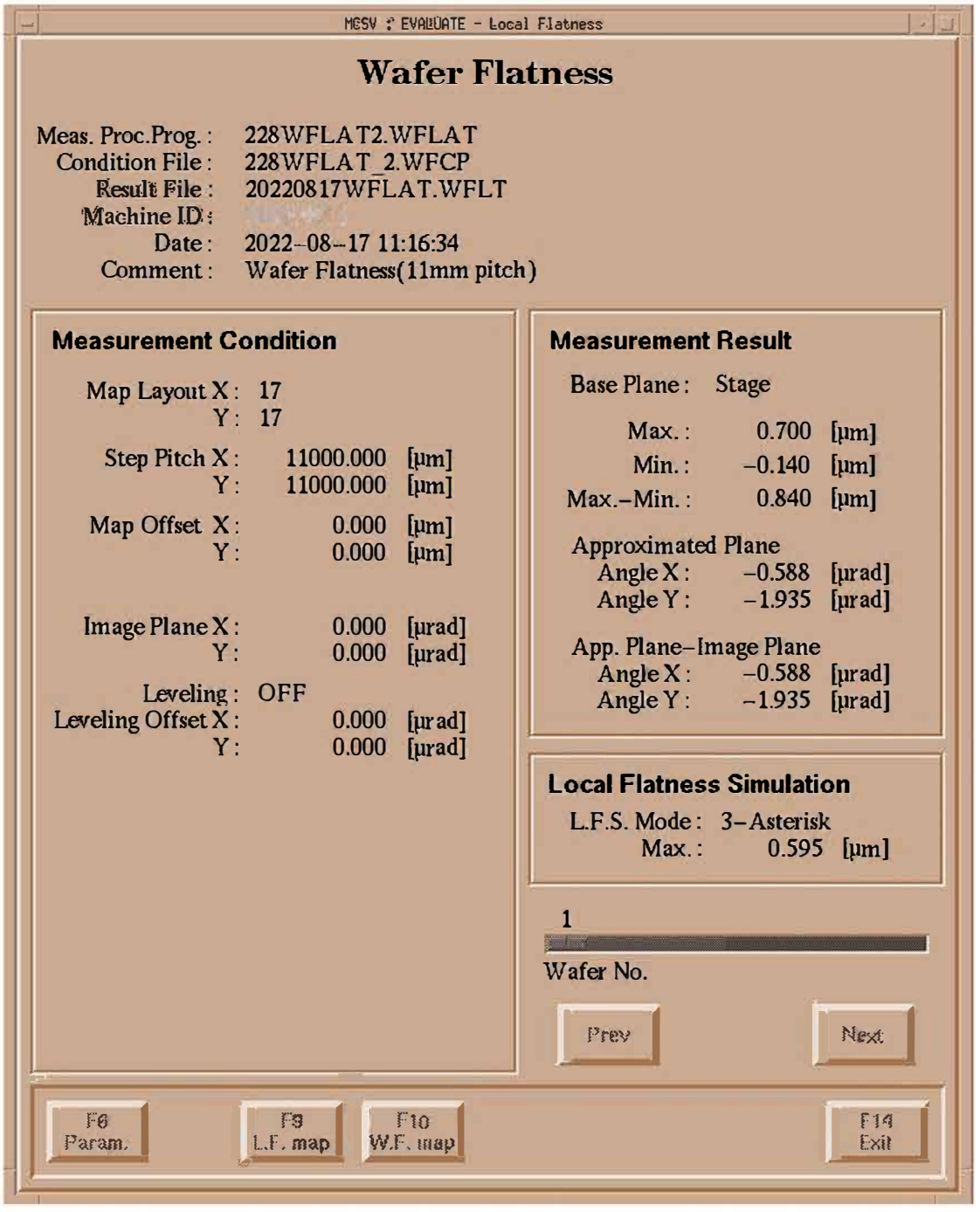
	project	data
1	AF rep	Max-min：0.05um
2	Dis	X：-10~13nm Y：-12~16nm
3	Fia ovl	X：20nm y：22nm
4	Flantness	Max-min：0.840um
5	Inc	TFD:140nm
6	Lamp	835mw/cm2
7	Lsa ovl	X：20nm y：34nm
8	Step	X：16nm y：16nm
9	Tele	Max：21nm
10	Wl rep	X：2.7um y：6.7um t：6.2um


MCSV : EVALUATE - Focus Repeatability
Focus Repeatability
Meas.Proc.Prog. : 228AFOCUS2.AFOCUS
Condition File : 228AFOCUS_CE_2.WFCP
Result File : 20200827AFOCUS_CE.WFI
Machine ID :
Date : 2022-08-27 10:08:46
Comment : Focus repeatability(Center)
Measurement Condition
Meas. Point Num. : 25
Intra-shot Repeat Count : 2
Measurement Result
Max Focus Repeatability
Max.-Min. : 0.050 [µm]
3Sigma : 0.106 [µm]
F10 Map
F14 Exit


MCSV : EVALUATE - Distortion Map
Correction Result
Meas.P.P. : 228USR2D.MSDISLSA
Cond.file : 228DIS_LSA_2.SMCP
Res.file : 081123_ID1_DIS.MESR
Mac.ID :
Date : 2022-11-23 11:25:17
Comm. :
Reticle : R2205HDISV5283A-1-02-1
Illum.ID :
Center shift Correction : Auto.
Rotation Correction : ON
Value : 0.951 [urad]
Reduction Correction : ON
Value : 0.488 [ppm]
Address X : -6000 [µm]
Y : 12000 [µm]
Max X : 0.013 [µm]
Y : 0.016 [µm]
Min X : -0.010 [µm]
Y : -0.012 [µm]
Max-Min X : 0.023 [µm]
Y : 0.028 [µm]
Max S : 0.016 [µm]
F13 Value/Grid
F14 Exit

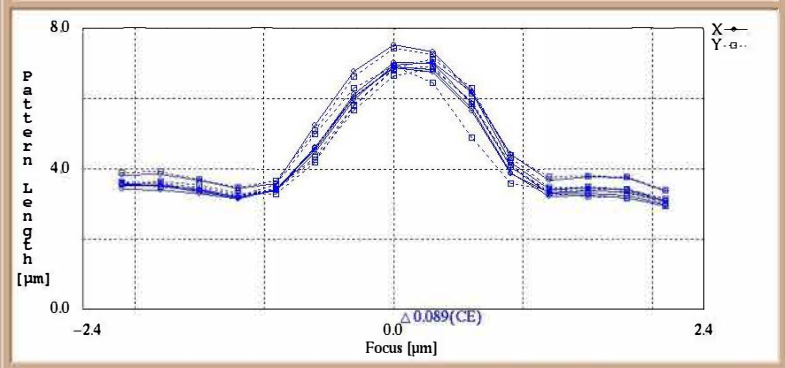

MCSV : EVALUATE - LSA Base Line
LSA Base Line
Meas.Proc.Prog. : 228USR2A.MSREGLSA
Condition File : 228REG05_LSA_2.SMCP
Result File : 220928_REG05_FIA_REP005
Machine ID :
Date : 2022-09-28 14:07:46
Comment : Baseline check[R2205HA Ver7.2]
Wafer Average[µm] X Y 3σ[µm] X Y
1 0.008 0.006 0.022 0.024
2 0.009 0.006 0.018 0.020
Total 0.009 0.006 0.020 0.022
Total Average, 3σ
EGA Parameter
Shot Analysis
Map Display Mode
Measured Data
Correction Contents
Each Wafer
Offset X
Scaling X
Orthogonality
Shot Scaling
Offset Y
Scaling Y
Rotation
Shot Rotation
F6 Param
F7 List
F10 Map
F14 Exit


MESV : EVALUATE - Local Flatness
Wafer Flatness
Meas. Proc.Prog. : 228WFLAT2.WFLAT
Condition File : 228WFLAT_2.WFCP
Result File : 20220817WFLAT.WFLT
Machine ID :
Date : 2022-08-17 11:16:34
Comment : Wafer Flatness(11mm pitch)
Measurement Condition
Map Layout X : 17
Y : 17
Step Pitch X : 11000.000 [µm]
Y : 11000.000 [µm]
Map Offset X : 0.000 [µm]
Y : 0.000 [µm]
Image Plane X : 0.000 [µrad]
Y : 0.000 [µrad]
Leveling : OFF
Leveling Offset X : 0.000 [µrad]
Y : 0.000 [µrad]
Measurement Result
Base Plane : Stage
Max. : 0.700 [µm]
Min. : -0.140 [µm]
Max.-Min. : 0.840 [µm]
Approximated Plane
Angle X : -0.588 [µrad]
Angle Y : -1.935 [µrad]
App. Plane-Image Plane
Angle X : -0.588 [µrad]
Angle Y : -1.935 [µrad]
Local Flatness Simulation
L.F.S. Mode : 3-Asterisk
Max. : 0.595 [µm]
1
Wafer No.
Prev
Next
F8 Param.
F9 L.F. map
F10 W.F. map
F14 Exit

M.S.V. : EVALUATE - Field Inclination

Field Inclination

No.	Locate [µm] X	Y	V	Best Focus [µm] H	V,H Ave.	V−H	Max Length [µm] X	Y	Inc. [µm]
1	−10701.00	−10701.00	0.013Min	0.084	0.048	−0.071	6.450	6.351	−0.030
2	−10701.00	10701.00	0.132	0.100	0.116	0.032	6.618	6.419	−0.013
3	0.00	0.00	0.093	0.086	0.089	0.007	7.098	6.995	0.000
4	10701.00	−10701.00	0.153Max	0.131	0.142	0.022	6.623	6.606	0.013
5	10701.00	10701.00	0.131	0.087	0.109	0.044	6.496	6.364	0.030



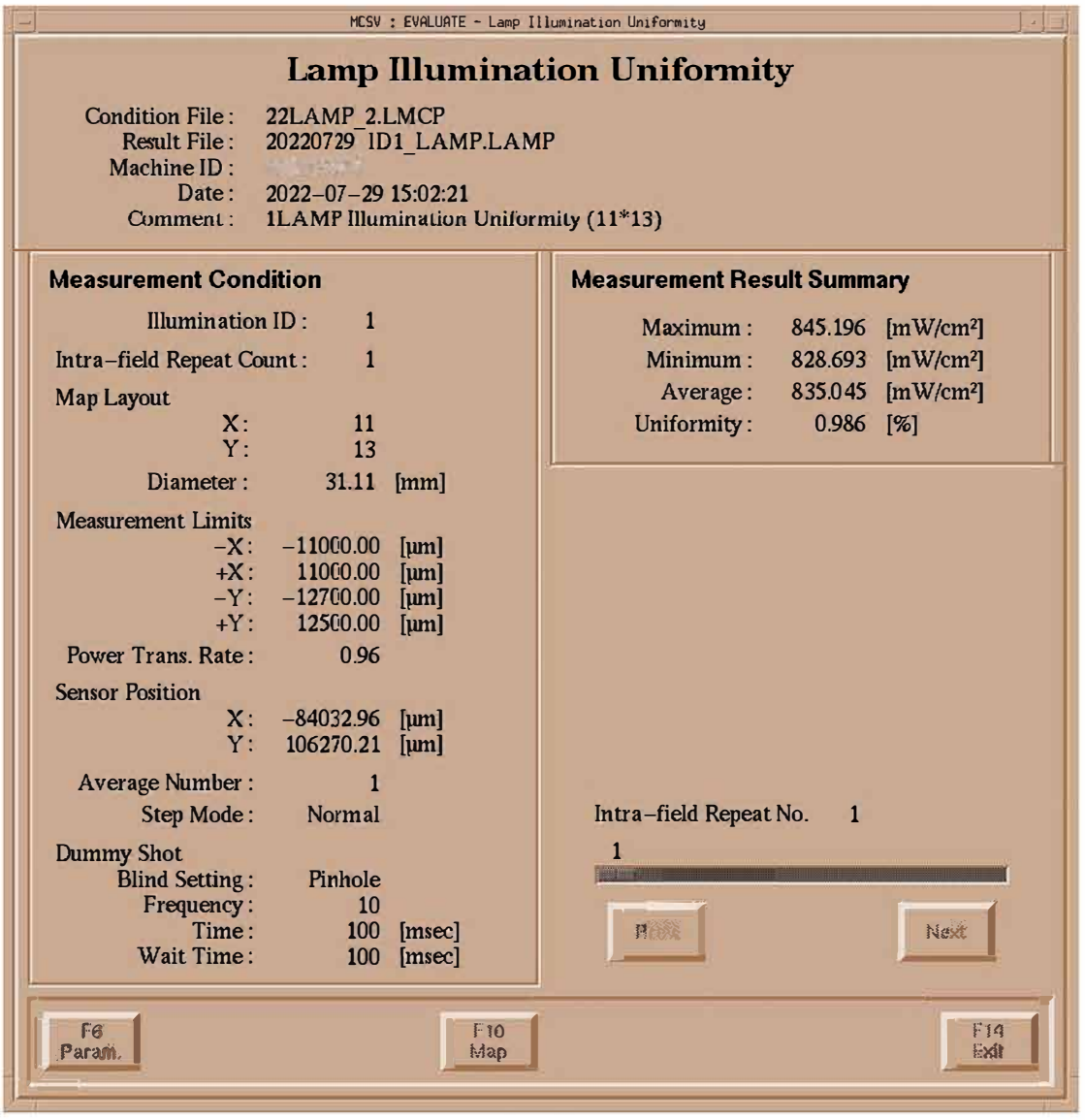
Meas.Proc.Prog. : 228INC2M8.MS05LSA
Condition File : 228INC●FF2G05H8_2
Result File : NIK●N01−20220602.M
Machine ID :
Date : 2022−06−02 04:01:28
Comment : INC 5 (0.35mic HV)[R2

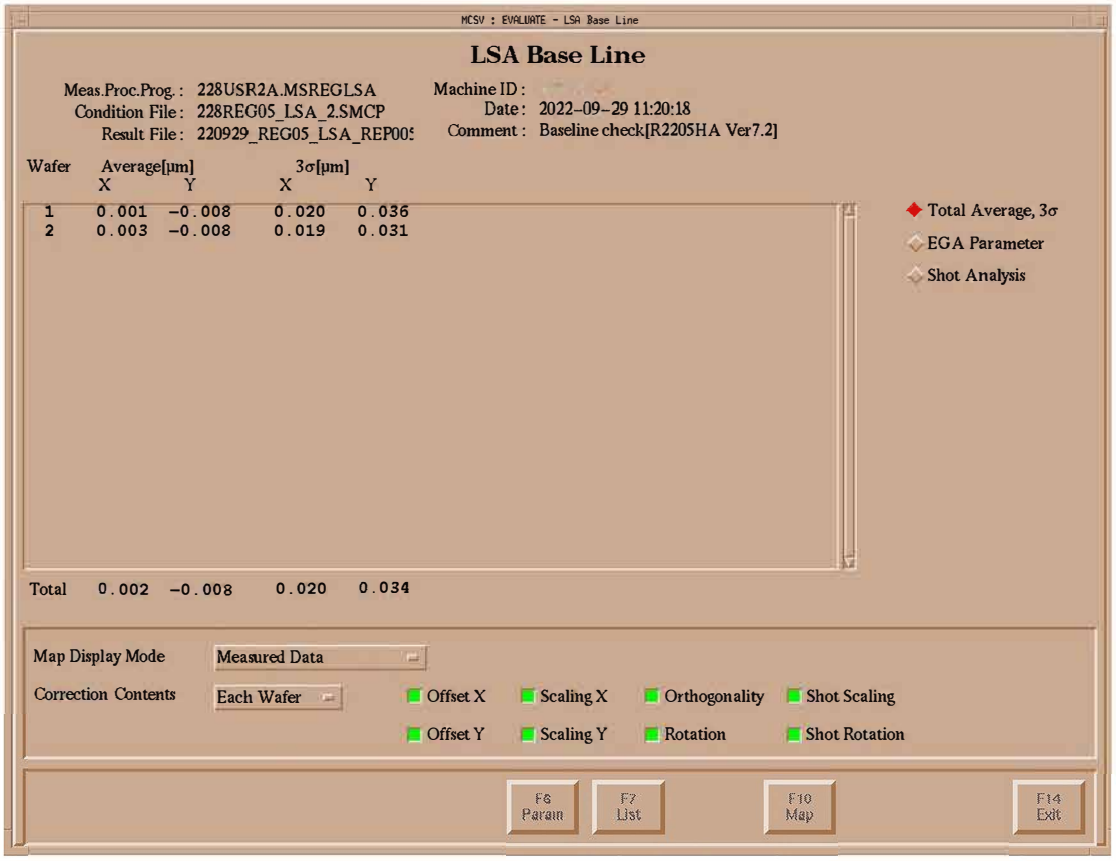
Reject Limit (Upper) :	12.000	[µm]
Reject Limit (Range) :	1.000	[µm]
Approximate Reject Limit :	1.000	[µm]
Focus Center on Exposure :	0.000	[µm]
Focus Step on Exposure :	0.300	[µm]
Focus Slice Level :	1.000	[µm]
Weight Dumping Rate :	1.000	
Angle adjustment Value X :	--------	[µrad]
Y :	--------	[µrad]
Angle X :	2.021	[µrad]
Angle Y :	0.806	[µrad]
Angle R :	−0.859	[µrad]
Angle P :	1.999	[µrad]
Max−Min :	0.140	[µm]
●urvature :	0.014	[µm]
UR−LL :	0.060	[µm]
UL−LR :	−0.026	[µm]

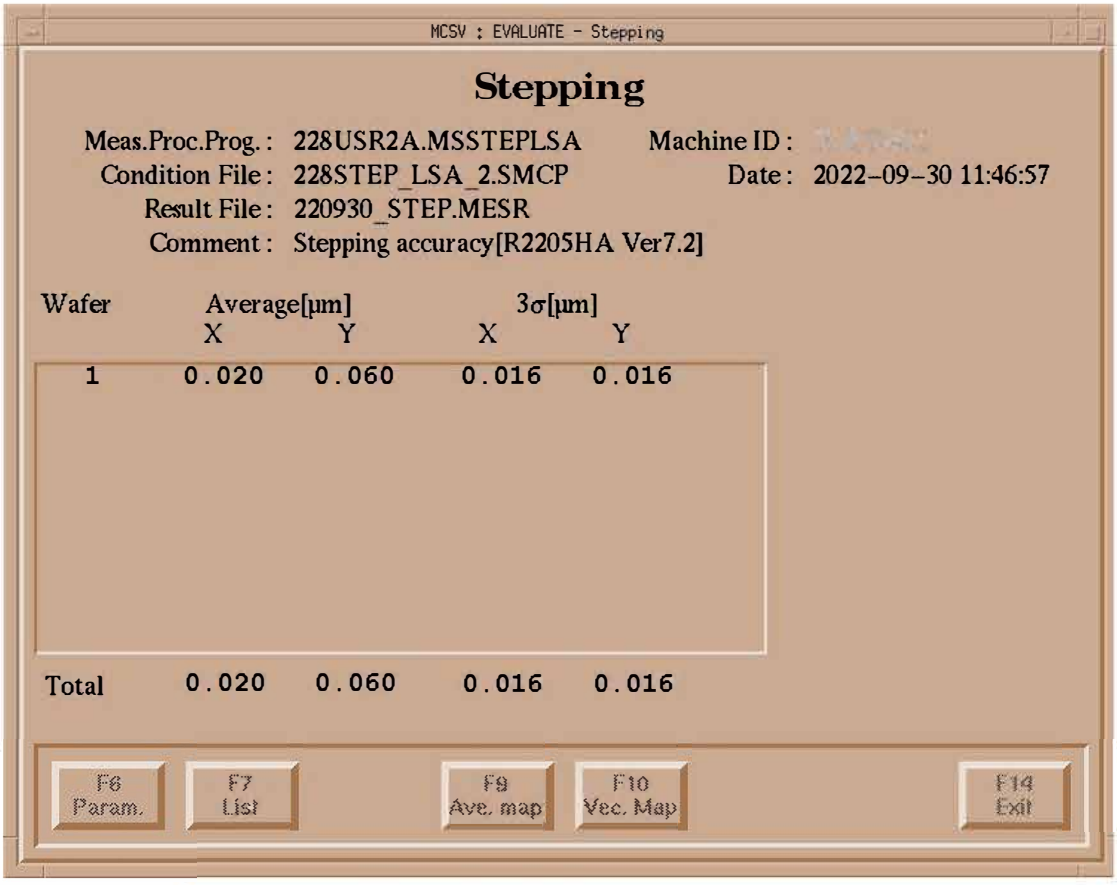
●bject Wafer
◇Total ◆Each Wafer
1
Wafer No.

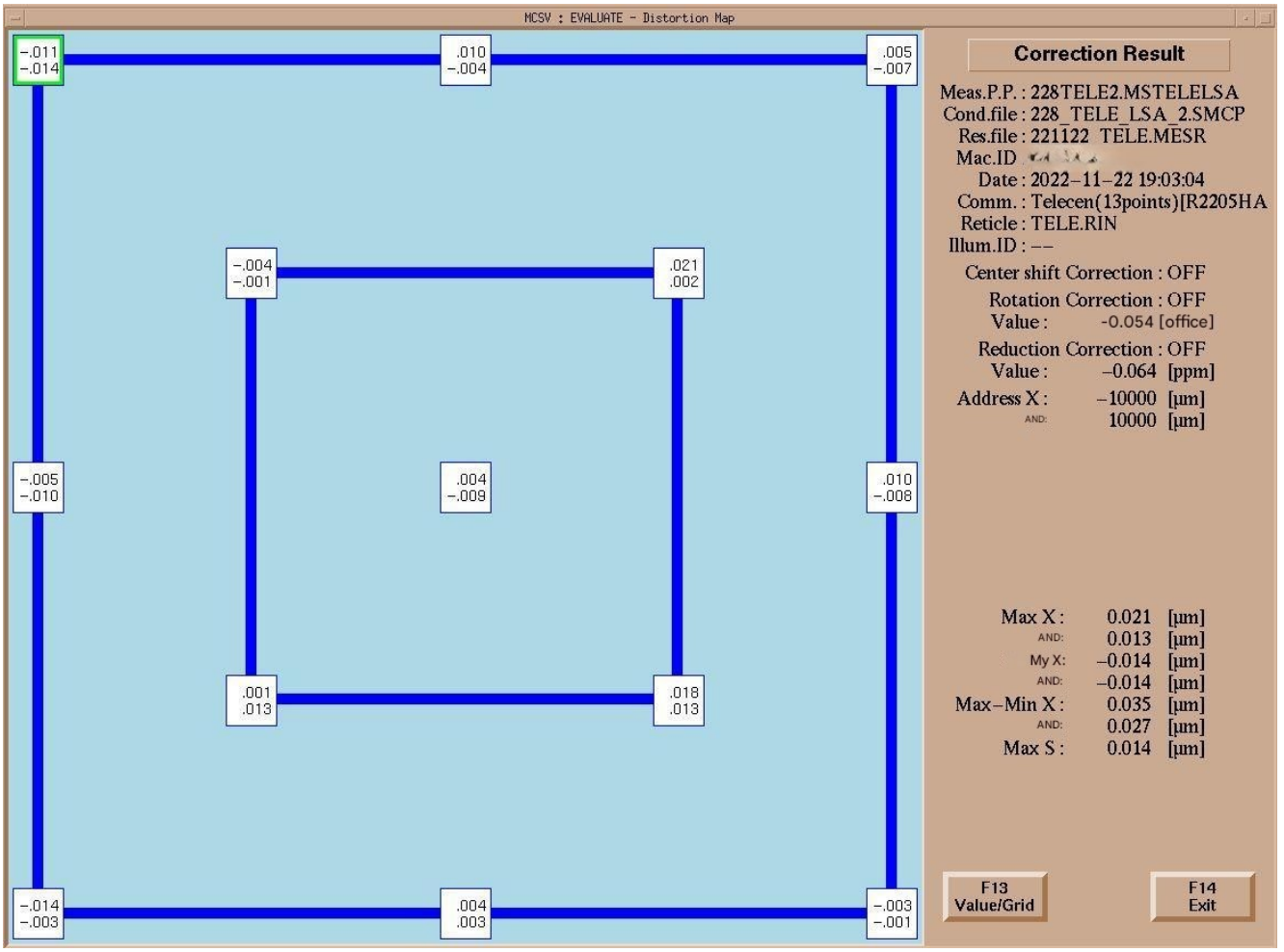
Prev Next

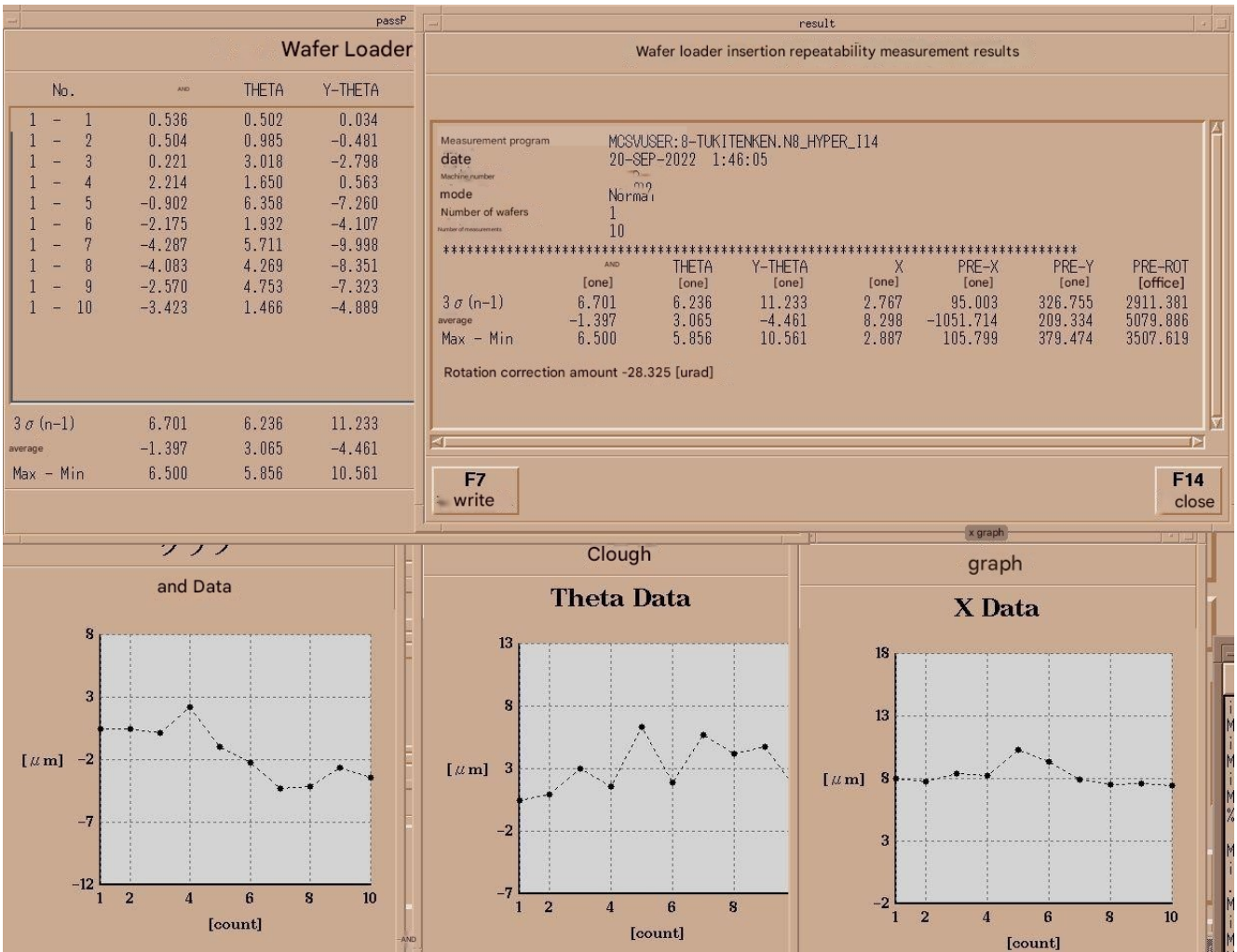
F6 Param. F7 List F8 Summary F9 Display F10 Map F14 Exit


MCSV : EVALUATE - Lamp Illumination Uniformity
Lamp Illumination Uniformity
Condition File : 22LAMP_2.LMCP
Result File : 20220729_ID1_LAMP.LAMP
Machine ID :
Date : 2022-07-29 15:02:21
Comment : 1LAMP Illumination Uniformity (11*13)
Measurement Condition
Illumination ID : 1
Intra-field Repeat Count : 1
Map Layout
X : 11
Y : 13
Diameter : 31.11 [mm]
Measurement Limits
-X : -11000.00 [µm]
+X : 11000.00 [µm]
-Y : -12700.00 [µm]
+Y : 12500.00 [µm]
Power Trans. Rate : 0.96
Sensor Position
X : -84032.96 [µm]
Y : 106270.21 [µm]
Average Number : 1
Step Mode : Normal
Dummy Shot
Blind Setting : Pinhole
Frequency : 10
Time : 100 [msec]
Wait Time : 100 [msec]
Measurement Result Summary
Maximum : 845.196 [mW/cm²]
Minimum : 828.693 [mW/cm²]
Average : 835.045 [mW/cm²]
Uniformity : 0.986 [%]
Intra-field Repeat No. 1
1
Next
F6 Param.
F10 Map
F14 Exit


MCSV : EVALUATE - LSA Base Line
LSA Base Line
Meas.Proc.Prog. : 228USR2A.MSREGLSA
Condition File : 228REG05_LSA_2.SMCP
Result File : 220929_REG05_LSA_REP00
Machine ID :
Date : 2022-09-29 11:20:18
Comment : Baseline check[R2205HA Ver7.2]
Wafer Average[µm] 3σ[µm]
X Y X Y
1 0.001 -0.008 0.020 0.036
2 0.003 -0.008 0.019 0.031
Total 0.002 -0.008 0.020 0.034
Total Average, 3σ
EGA Parameter
Shot Analysis
Map Display Mode
Measured Data
Correction Contents
Each Wafer
Offset X
Scaling X
Orthogonality
Shot Scaling
Offset Y
Scaling Y
Rotation
Shot Rotation
F6 Param
F7 List
F10 Map
F14 Exit


MCSV : EVALUATE - Stepping
Stepping
Meas.Proc.Prog. : 228USR2A.MSSTEPLSA
Condition File : 228STEP_LSA_2.SMCP
Result File : 220930_STEP.MESR
Comment : Stepping accuracy[R2205HA Ver7.2]
Machine ID :
Date : 2022-09-30 11:46:57
Wafer Average[µm] 3σ[µm]
X Y X Y
1 0.020 0.060 0.016 0.016
Total 0.020 0.060 0.016 0.016
F6 Param.
F7 List
F9 Ave. map
F10 Vec. Map
F14 Exit


MCSV : EVALUATE - Distortion Map
-.011
-.014
.010
-.004
.005
-.007
-.004
-.001
.021
.002
-.005
-.010
.004
-.009
.010
-.008
.001
.013
.018
.013
-.014
-.003
.004
.003
-.003
-.001
Correction Result
Meas.P.P. : 228TELE2.MSTELELSA
Cond.file : 228_TELE_LSA_2.SMCP
Res.file : 221122 TELE.MESR
Mac.ID
Date : 2022-11-22 19:03:04
Comm. : Telecen(13points)[R2205HA
Reticle : TELE.RIN
Illum.ID : --
Center shift Correction : OFF
Rotation Correction : OFF
Value : -0.054 [office]
Reduction Correction : OFF
Value : -0.064 [ppm]
Address X : -10000 [µm]
AND: 10000 [µm]
Max X : 0.021 [µm]
AND: 0.013 [µm]
My X: -0.014 [µm]
AND: -0.014 [µm]
Max-Min X : 0.035 [µm]
AND: 0.027 [µm]
Max S : 0.014 [µm]
F13
Value/Grid
F14
Exit


passP
Wafer Loader
No. AND THETA Y-THETA
1 - 1 0.536 0.502 0.034
1 - 2 0.504 0.985 -0.481
1 - 3 0.221 3.018 -2.798
1 - 4 2.214 1.650 0.563
1 - 5 -0.902 6.358 -7.260
1 - 6 -2.175 1.932 -4.107
1 - 7 -4.287 5.711 -9.998
1 - 8 -4.083 4.269 -8.351
1 - 9 -2.570 4.753 -7.323
1 - 10 -3.423 1.466 -4.889
3σ (n-1) 6.701 6.236 11.233
average -1.397 3.065 -4.461
Max - Min 6.500 5.856 10.561
result
Wafer loader insertion repeatability measurement results
Measurement program MCSVUSER:8-TUKITENKEN.N8_HYPER_I14
date 20-SEP-2022 1:46:05
Machine number
mode Normal
Number of wafers 1
Number of measurements 10
AND THETA Y-THETA X PRE-X PRE-Y PRE-ROT
[one] [one] [one] [one] [one] [one] [office]
3σ (n-1) 6.701 6.236 11.233 2.767 95.003 326.755 2911.381
average -1.397 3.065 -4.461 8.298 -1051.714 209.334 5079.886
Max - Min 6.500 5.856 10.561 2.887 105.799 379.474 3507.619
Rotation correction amount -28.325 [urad]
F7
write
F14
close
and Data
[µm]
[count]
Clough
Theta Data
[µm]
[count]
x graph
graph
X Data
[µm]
[count]